Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62/ TO-243) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110X.

2. Features and benefits

- SOT89 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High efficiency leading to less heat generation
- AEC-Q101 qualified

3. Applications

- · Major application segments:
 - Automotive 42 V power
 - Telecom infrastructure
 - Industrial
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)
- DC-to-DC converter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	165	200	mΩ



100 V, 1 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	B — () E
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package	kage				
	Name	Description	Version			
PBSS8110X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS8110X	%4B

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	120	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	Α
I _B	base current			-	300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.55	W
			[2]	-	1.4	W
			[3]	-	2	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

100 V, 1 A NPN low VCEsat transistor

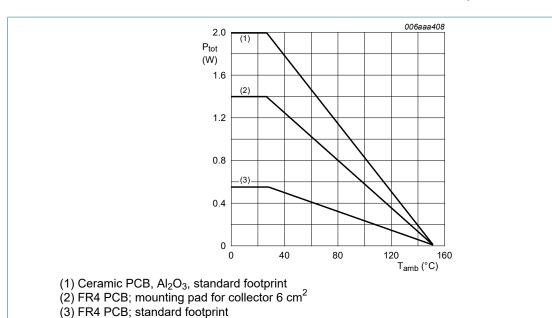


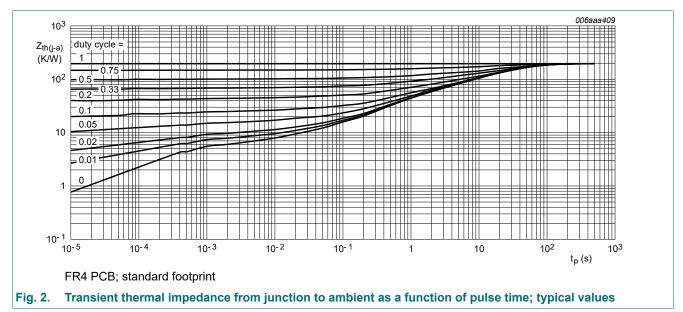
Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	[1] [2] [3]	[1]	-	-	227	K/W
	junction to ambient		[2]	-	-	89	K/W
			[3]	-	-	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



100 V, 1 A NPN low VCEsat transistor

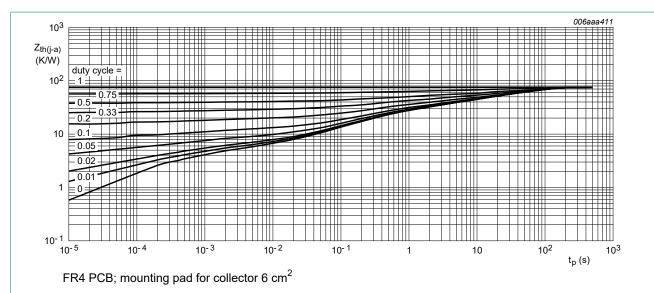


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

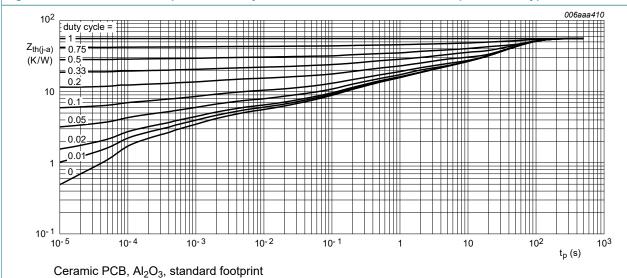


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 1 mA; T _{amb} = 25 °C	150	-	-	
		V _{CE} = 10 V; I _C = 250 mA; T _{amb} = 25 °C	150	-	500	
		V_{CE} = 10 V; I_{C} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	-	-	

PBSS8110X

100 V, 1 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	-	-	40	mV
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	120	mV
		I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	165	200	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; T _{amb} = 25 °C	-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 10 V; I _C = 1 A; T _{amb} = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 0.025 A; I _{Boff} = -0.025 A; T _{amb} = 25 °C	-	25	-	ns
t _r	rise time		-	220	-	ns
t _{on}	turn-on time		-	245	-	ns
t _s	storage time		-	365	-	ns
t _f	fall time		-	185	-	ns
t _{off}	turn-off time		-	550	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	7.5	pF

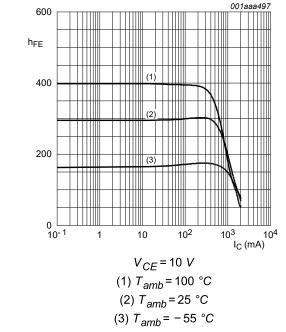


Fig. 5. DC current gain as a function of collector current; typical values

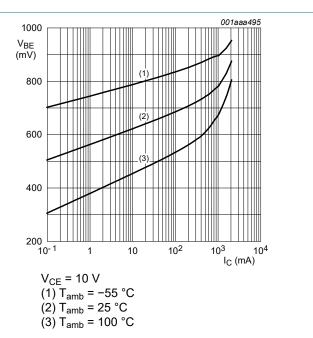


Fig. 6. Base-emitter voltage as a function of collector current; typical values

100 V, 1 A NPN low VCEsat transistor

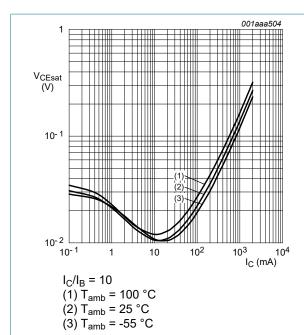


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

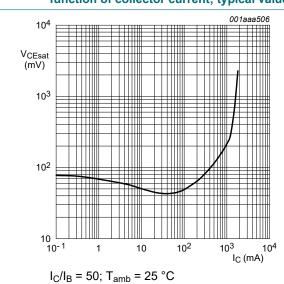


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

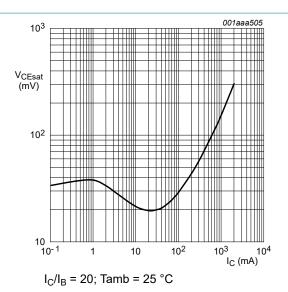
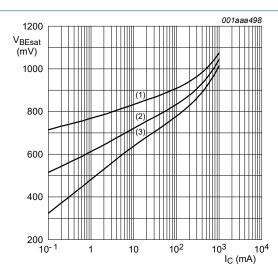


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

100 V, 1 A NPN low VCEsat transistor

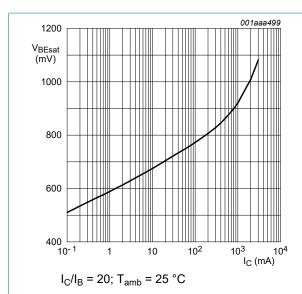
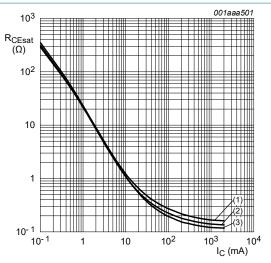


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



$$I_{C}/I_{B} = 10$$

(1) $T_{amb} = 100 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = -55 \,^{\circ}C$

(3) 1_{amb} = -33 C

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

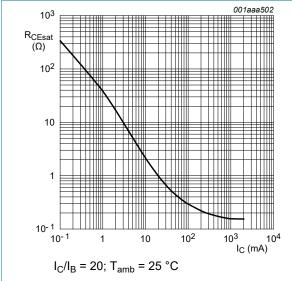


Fig. 13. Equivalent on-resistance as a function of collector current; typical values

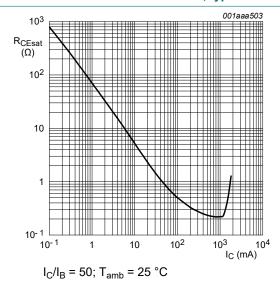
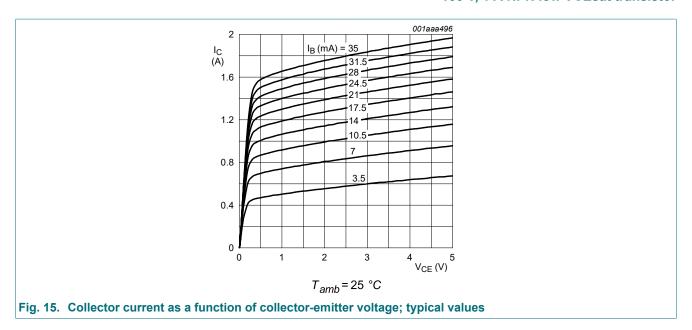
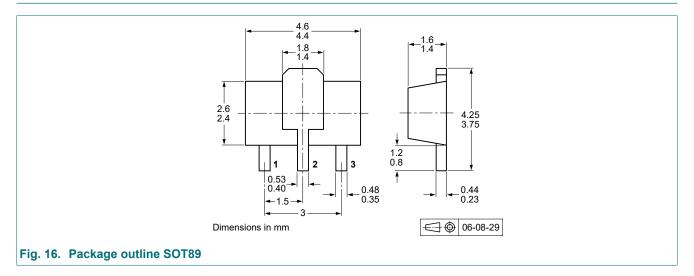


Fig. 14. Equivalent on-resistance as a function of collector current; typical values

100 V, 1 A NPN low VCEsat transistor

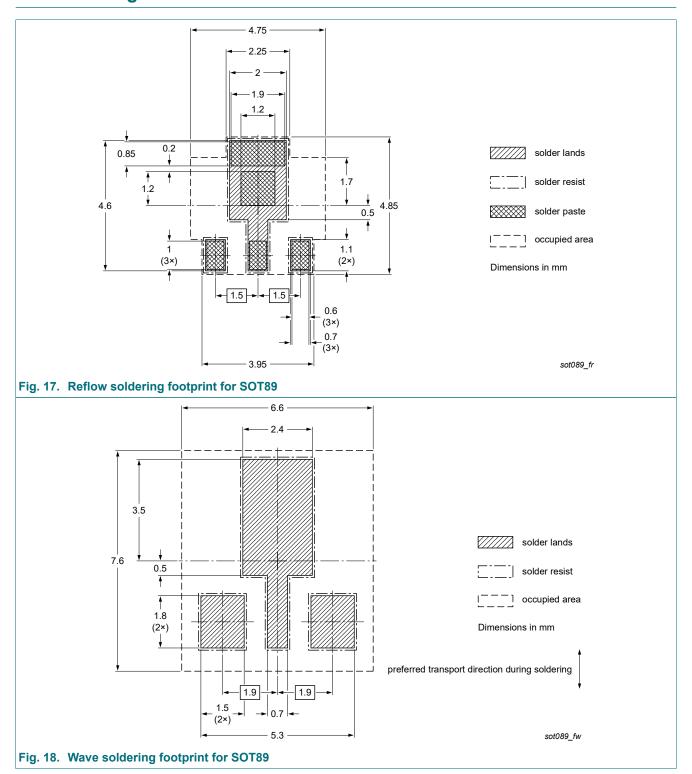


11. Package outline



100 V, 1 A NPN low VCEsat transistor

12. Soldering



9 / 12

100 V, 1 A NPN low VCEsat transistor

13. Revision history

Table 8. Revision history

Table of Revision metery							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS8110X v.3	20250703	Product data sheet	-	PBSS8110X_2			
Modifications	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 						
PBSS8110X_2	20091211	Product data sheet	-	PBSS8110X_1			
PBSS8110X_1	20050511	Product data sheet	-	-			

100 V, 1 A NPN low VCEsat transistor

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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100 V, 1 A NPN low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	. 2
9.	Thermal characteristics	. 3
10.	Characteristics	4
11.	Package outline	. 8
12.	Soldering	. 9
13.	Revision history	10
14.	Legal information	11

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